

ABSTRACT

A method and system for providing an interconnect on a semiconductor device is disclosed. The method and system comprises providing a semiconductor substrate with a plurality of device structures thereon and providing at least one slot in the semiconductor substrate. The method and system include providing a metal within the at least one slot.

This first metal in a preferred embodiment consists of three depositions of metal when sputtered, with the first two depositions being buried in the silicon prior to a dielectric and a third deposition of what is called the first metal layer. This third deposition provides the normal interconnect pattern as it normally is patterned in standard metalization schemes.